

Alexander Y Polyakov

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

262
papers

5,303
citations

37
h-index

57
g-index

266
ext. papers

5,831
ext. citations

2.8
avg, IF

5.49
L-index

#	Paper	IF	Citations
262	Communication Electron-Beam Stimulated Release of Dislocations from Pinning Sites in GaN. <i>ECS Journal of Solid State Science and Technology</i> , 2022 , 11, 015003	2	
261	Betavoltaic cell based on Ni/ β -Ga ₂ O ₃ and ⁶³ Ni source. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2022 , 40, 010401	2.9	1
260	Deep level defect states in β - β and e-Ga ₂ O ₃ crystals and films: Impact on device performance. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2022 , 40, 020804	2.9	11
259	Structural and electrical properties of thick β -Ga ₂ O ₃ grown on GaN/sapphire templates. <i>APL Materials</i> , 2022 , 10, 061102	5.7	1
258	1 GeV proton damage in β -Ga ₂ O ₃ . <i>Journal of Applied Physics</i> , 2021 , 130, 185701	2.5	1
257	On the relation between mobile ion kinetics, device design, and doping in double-cation perovskite solar cells. <i>Applied Physics Letters</i> , 2021 , 118, 093501	3.4	1
256	Parasitic p-n junctions formed at V-pit defects in p-GaN. <i>Journal of Applied Physics</i> , 2021 , 129, 155702	2.5	1
255	Review Radiation Damage in Wide and Ultra-Wide Bandgap Semiconductors. <i>ECS Journal of Solid State Science and Technology</i> , 2021 , 10, 055008	2	19
254	Experimental estimation of electron-hole pair creation energy in β -Ga ₂ O ₃ . <i>Applied Physics Letters</i> , 2021 , 118, 202106	3.4	8
253	Electrical properties and deep trap spectra in Ga ₂ O ₃ films grown by halide vapor phase epitaxy on p-type diamond substrates. <i>Journal of Applied Physics</i> , 2021 , 129, 185701	2.5	6
252	Crystal orientation dependence of deep level spectra in proton irradiated bulk β -Ga ₂ O ₃ . <i>Journal of Applied Physics</i> , 2021 , 130, 035701	2.5	4
251	Halide Vapor Phase Epitaxy of In ₂ O ₃ and (In _{1-x} Ga _x) ₂ O ₃ on Sapphire Substrates and GaN/Al ₂ O ₃ Templates. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2021 , 218, 2000442	1.6	2
250	Estimations of Activation Energy for Dislocation Mobility in p-GaN. <i>ECS Journal of Solid State Science and Technology</i> , 2021 , 10, 026004	2	1
249	Dislocations introduced in n-GaN at room temperature cause conductivity inversion. <i>Journal of Alloys and Compounds</i> , 2021 , 877, 160281	5.7	2
248	Diffusion of dopants and impurities in β -Ga ₂ O ₃ . <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2021 , 39, 060801	2.9	8
247	Photosensitivity of Ga ₂ O ₃ Schottky diodes: Effects of deep acceptor traps present before and after neutron irradiation. <i>APL Materials</i> , 2020 , 8, 111105	5.7	13
246	Anisotropy of hydrogen plasma effects in bulk n-type β -Ga ₂ O ₃ . <i>Journal of Applied Physics</i> , 2020 , 127, 175702	2.5	14

245	In Situ Transmission Electron Microscopy Observations of Forward Bias Degradation of Vertical Geometry EGa_2O_3 Rectifiers. <i>ECS Journal of Solid State Science and Technology</i> , 2020 , 9, 055008	2	3
244	Assessing mobile ions contributions to admittance spectra and current-voltage characteristics of 3D and 2D/3D perovskite solar cells. <i>Solar Energy Materials and Solar Cells</i> , 2020 , 215, 110670	6.4	9
243	Pulsed fast reactor neutron irradiation effects in Si doped n-type EGa_2O_3 . <i>Journal Physics D: Applied Physics</i> , 2020 , 53, 274001	3	13
242	Electric field dependence of major electron trap emission in bulk EGa_2O_3 : Poole-Frenkel effect versus phonon-assisted tunneling. <i>Journal Physics D: Applied Physics</i> , 2020 , 53, 304001	3	9
241	Editors' Choice Electrical Properties and Deep Traps in EGa_2O_3 :Sn Films Grown on Sapphire by Halide Vapor Phase Epitaxy. <i>ECS Journal of Solid State Science and Technology</i> , 2020 , 9, 045003	2	10
240	Ion Dynamics in Single and Multi-Cation Perovskite. <i>ECS Journal of Solid State Science and Technology</i> , 2020 , 9, 065015	2	3
239	Preface JSS Focus Issue on Gallium Oxide Based Materials and Devices II. <i>ECS Journal of Solid State Science and Technology</i> , 2020 , 9, 060001	2	0
238	Role of hole trapping by deep acceptors in electron-beam-induced current measurements in EGa_2O_3 vertical rectifiers. <i>Journal Physics D: Applied Physics</i> , 2020 , 53, 495108	3	11
237	Effects of 5 MeV electron irradiation on deep traps and electroluminescence from near-UV InGaN/GaN single quantum well light-emitting diodes with and without InAlN superlattice underlayer. <i>Journal Physics D: Applied Physics</i> , 2020 , 53, 445111	3	3
236	Ultrawide-Bandgap p-n Heterojunction of Diamond/ EGa_2O_3 for a Solar-Blind Photodiode. <i>ECS Journal of Solid State Science and Technology</i> , 2020 , 9, 045004	2	20
235	Effects of InAlN underlayer on deep traps detected in near-UV InGaN/GaN single quantum well light-emitting diodes. <i>Journal of Applied Physics</i> , 2019 , 126, 125708	2.5	14
234	Radiation damage effects in Ga_2O_3 materials and devices. <i>Journal of Materials Chemistry C</i> , 2019 , 7, 10241	2.1	90
233	Electrical Properties, Deep Trap and Luminescence Spectra in Semi-Insulating, Czochralski EGa_2O_3 (Mg). <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, Q3019-Q3023	2	25
232	Defects at the surface of EGa_2O_3 produced by Ar plasma exposure. <i>APL Materials</i> , 2019 , 7, 061102	5.7	25
231	Deep trap analysis in green light emitting diodes: Problems and solutions. <i>Journal of Applied Physics</i> , 2019 , 125, 215701	2.5	5
230	Deep trap spectra of Sn-doped EGa_2O_3 grown by halide vapor phase epitaxy on sapphire. <i>APL Materials</i> , 2019 , 7, 051103	5.7	22
229	Electrical Properties, Deep Levels and Luminescence Related to Fe in Bulk Semi-Insulating EGa_2O_3 Doped with Fe. <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, Q3091-Q3096	2	19
228	Deep traps and persistent photocapacitance in $(\text{Al}_{0.14}\text{Ga}_{0.86})_2\text{O}_3/\text{Ga}_2\text{O}_3$ heterojunctions. <i>Journal of Applied Physics</i> , 2019 , 125, 095702	2.5	1

227	Hydrogen plasma treatment of EGa_2O_3 : Changes in electrical properties and deep trap spectra. <i>Applied Physics Letters</i> , 2019 , 115, 032101	3.4	29
226	Effects of Hydrogen Plasma Treatment Condition on Electrical Properties of EGa_2O_3 . <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, P661-P666	2	4
225	III-Nitride Nanowires as Building Blocks for Advanced Light Emitting Diodes. <i>Physica Status Solidi (B): Basic Research</i> , 2019 , 256, 1800589	1.3	4
224	Defect States Determining Dynamic Trapping-Detrapping in EGa_2O_3 Field-Effect Transistors. <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, Q3013-Q3018	2	19
223	Betavoltaic battery performance: Comparison of modeling and experiment. <i>Applied Radiation and Isotopes</i> , 2018 , 137, 184-189	1.7	21
222	Trapping Phenomena in InAlN/GaN High Electron Mobility Transistors. <i>ECS Journal of Solid State Science and Technology</i> , 2018 , 7, Q1-Q7	2	9
221	Point defect induced degradation of electrical properties of Ga_2O_3 by 10 MeV proton damage. <i>Applied Physics Letters</i> , 2018 , 112, 032107	3.4	72
220	Temperature Dependence of Low-Energy Electron Beam Irradiation Effect on Optical Properties of MQW InGaN/GaN Structures. <i>Physica Status Solidi (B): Basic Research</i> , 2018 , 255, 1700646	1.3	2
219	Compensation and persistent photocapacitance in homoepitaxial Sn-doped EGa_2O_3 . <i>Journal of Applied Physics</i> , 2018 , 123, 115702	2.5	57
218	Enhanced luminescence of CsPbBr perovskite nanocrystals on stretchable templates with Au/SiO plasmonic nanoparticles. <i>Optics Letters</i> , 2018 , 43, 2352-2355	3	6
217	Electrical Properties of Bulk, Non-Polar, Semi-Insulating M-GaN Grown by the Ammonothermal Method. <i>ECS Journal of Solid State Science and Technology</i> , 2018 , 7, P260-P265	2	11
216	Quantum Barrier Growth Temperature Affects Deep Traps Spectra of InGaN Blue Light Emitting Diodes. <i>ECS Journal of Solid State Science and Technology</i> , 2018 , 7, Q80-Q84	2	7
215	Diffusion length of non-equilibrium minority charge carriers in EGa_2O_3 measured by electron beam induced current. <i>Journal of Applied Physics</i> , 2018 , 123, 185704	2.5	37
214	Defect States Induced in GaN-Based Green Light Emitting Diodes by Electron Irradiation. <i>ECS Journal of Solid State Science and Technology</i> , 2018 , 7, P323-P328	2	9
213	Recombination properties of dislocations in GaN. <i>Journal of Applied Physics</i> , 2018 , 123, 161543	2.5	21
212	Large Area Polymer Composite Films Embedded with Colloidal Quantum Dots for Efficient White Light Generation. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018 , 215, 1700644	1.6	7
211	Trap states in multication mesoscopic perovskite solar cells: A deep levels transient spectroscopy investigation. <i>Applied Physics Letters</i> , 2018 , 113, 263501	3.4	24
210	Electrical properties, structural properties, and deep trap spectra of thin EGa_2O_3 films grown by halide vapor phase epitaxy on basal plane sapphire substrates. <i>APL Materials</i> , 2018 , 6, 121110	5.7	26

209	Enhanced Luminescence of InGaN Quantum Well Structures with Localized Surface Plasmon by Using Sputter-Fabricated Ag Nanoparticles in an Ionic Liquid. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018 , 215, 1800516	1.6	1
208	Electrical properties of bulk semi-insulating Γ -Ga ₂ O ₃ (Fe). <i>Applied Physics Letters</i> , 2018 , 113, 142102	3.4	59
207	Hole traps and persistent photocapacitance in proton irradiated Γ -Ga ₂ O ₃ films doped with Si. <i>APL Materials</i> , 2018 , 6, 096102	5.7	50
206	Performance of InGaN/GaN Light Emitting Diodes with n-GaN Layer Embedded with SiO ₂ Nano-Particles. <i>Applied Sciences (Switzerland)</i> , 2018 , 8, 1574	2.6	3
205	Defects responsible for charge carrier removal and correlation with deep level introduction in irradiated Γ -Ga ₂ O ₃ . <i>Applied Physics Letters</i> , 2018 , 113, 092102	3.4	46
204	Current relaxation analysis in AlGaIn/GaN high electron mobility transistors. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2017 , 35, 011207	1.3	7
203	Effect of nanopillar sublayer embedded with SiO ₂ on deep traps in green GaN/InGaIn light emitting diodes. <i>Journal of Applied Physics</i> , 2017 , 121, 045108	2.5	9
202	Changes in electron and hole traps in GaN-based light emitting diodes from near-UV to green spectral ranges. <i>Applied Physics Letters</i> , 2017 , 110, 192107	3.4	16
201	Defects responsible for lifetime degradation in electron irradiated n-GaN grown by hydride vapor phase epitaxy. <i>Applied Physics Letters</i> , 2017 , 110, 112102	3.4	21
200	Deep Electron and Hole Traps in Electron-Irradiated Green GaN/InGaIn Light Emitting Diodes. <i>ECS Journal of Solid State Science and Technology</i> , 2017 , 6, Q127-Q131	2	9
199	Gate-Lag in AlGaIn/GaN High Electron Mobility Transistors: A Model of Charge Capture. <i>ECS Journal of Solid State Science and Technology</i> , 2017 , 6, S3034-S3039	2	10
198	Degradation-induced low frequency noise and deep traps in GaN/InGaIn near-UV LEDs. <i>Applied Physics Letters</i> , 2017 , 111, 062103	3.4	13
197	Point defects controlling non-radiative recombination in GaN blue light emitting diodes: Insights from radiation damage experiments. <i>Journal of Applied Physics</i> , 2017 , 122, 115704	2.5	19
196	Ag/SiO ₂ nanoparticle-based plasmonic enhancement of light output in nanohole-patterned InGaIn/GaN blue light-emitting diodes. <i>Japanese Journal of Applied Physics</i> , 2017 , 56, 100305	1.4	1
195	Electron irradiation of near-UV GaN/InGaIn light emitting diodes. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017 , 214, 1700372	1.6	10
194	Deep Electron Traps Responsible for Higher Quantum Efficiency in Improved GaN/InGaIn Light Emitting Diodes Embedded with SiO ₂ Nanoparticles. <i>ECS Journal of Solid State Science and Technology</i> , 2016 , 5, Q274-Q277	2	13
193	Review on Ionizing Radiation Damage Effects on GaN Devices. <i>ECS Journal of Solid State Science and Technology</i> , 2016 , 5, Q35-Q60	2	182
192	Radiation enhanced basal plane dislocation glide in GaN. <i>Japanese Journal of Applied Physics</i> , 2016 , 55, 05FM03	1.4	9

191	Electrical, luminescent, and deep trap properties of Si doped n-GaN grown by pendeo epitaxy. <i>Journal of Applied Physics</i> , 2016 , 119, 015103	2.5	23
190	Studies of deep level centers determining the diffusion length in epitaxial layers and crystals of undoped n-GaN. <i>Journal of Applied Physics</i> , 2016 , 119, 205109	2.5	23
189	Deep traps and instabilities in AlGaIn/GaN high electron mobility transistors on Si substrates. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2016 , 34, 041216	1.3	13
188	Electrical, Luminescent and Structural Properties of Nanopillar GaN/InGaIn Multi-Quantum-Well Structures Prepared by Dry Etching. <i>ECS Journal of Solid State Science and Technology</i> , 2016 , 5, Q165-Q170	2	8
187	Deep Traps in AlGaIn/GaN High Electron Mobility Transistors on SiC. <i>ECS Journal of Solid State Science and Technology</i> , 2016 , 5, Q260-Q265	2	8
186	Electron traps as major recombination centers in n-GaN films grown by metalorganic chemical vapor deposition. <i>Applied Physics Express</i> , 2016 , 9, 061002	2.4	13
185	Performance enhancement of GaN-based light emitting diodes by the interaction with localized surface plasmons. <i>Nano Energy</i> , 2015 , 13, 140-173	17.1	37
184	Improved GaN films with low background doping and low deep trap density grown by hydride vapor phase epitaxy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2015 , 12, 341-344		
183	Device performance of inverted polymer solar cells with AgSiO ₂ nanoparticles in active layer. <i>Optics Express</i> , 2015 , 23, A211-8	3.3	11
182	Movement of basal plane dislocations in GaN during electron beam irradiation. <i>Applied Physics Letters</i> , 2015 , 106, 132101	3.4	19
181	Deep level transient spectroscopy in III-Nitrides: Decreasing the effects of series resistance. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2015 , 33, 061203	1.3	41
180	Photoluminescence enhancement by localized surface plasmons in AlGaIn/GaN/AlGaIn double heterostructures. <i>Physica Status Solidi - Rapid Research Letters</i> , 2015 , 9, 575-579	2.5	4
179	EBIC investigations of dislocations in ELOG GaN. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2015 , 12, 1132-1135		5
178	Deep traps in GaN-based structures as affecting the performance of GaN devices. <i>Materials Science and Engineering Reports</i> , 2015 , 94, 1-56	30.9	139
177	Enhanced optical properties of nanopillar light-emitting diodes by coupling localized surface plasmon of Ag/SiO ₂ nanoparticles. <i>Applied Physics Express</i> , 2015 , 8, 092002	2.4	6
176	Facile fabrication of free-standing light emitting diode by combination of wet chemical etchings. <i>ACS Applied Materials & Interfaces</i> , 2014 , 6, 985-9	9.5	15
175	Radiation Damage in GaN-Based Materials and Devices 2014 , 345-387		3
174	Spatial location of the Ec-0.6 eV electron trap in AlGaIn/GaN heterojunctions. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2014 , 32, 050602	1.3	18

173	Hydride vapor phase GaN films with reduced density of residual electrons and deep traps. <i>Journal of Applied Physics</i> , 2014 , 115, 183706	2.5	11
172	Electrical Characteristics and Deep Traps Spectra of Undoped GaN Films Grown on Si Using Different Strain-Relieving Buffer Types. <i>IEEE Nanotechnology Magazine</i> , 2014 , 13, 151-159	2.6	2
171	Facile low-temperature synthesis of ZnO nanopyramid and its application to photocatalytic degradation of methyl orange dye under UV irradiation. <i>Materials Letters</i> , 2014 , 133, 224-227	3.3	26
170	Low energy electron beam irradiation effect on optical properties of nanopillar MQW InGaN/GaN structures 2014 ,		1
169	Enhanced optical output performance in InGaN/GaN light-emitting diode embedded with SiO ₂ nanoparticles. <i>Optics Express</i> , 2014 , 22, 21454-9	3.3	9
168	Deep hole traps in undoped n-GaN films grown by hydride vapor phase epitaxy. <i>Journal of Applied Physics</i> , 2014 , 115, 223702	2.5	34
167	Structural defects responsible for excessive leakage current in Schottky diodes prepared on undoped n-GaN films grown by hydride vapor phase epitaxy. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2014 , 32, 051212	1.3	4
166	Microcathodoluminescence spectra evolution for planar and nanopillar multiquantum-well GaN-based structures as a function of electron irradiation dose. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2014 , 32, 011207	1.3	7
165	Review of radiation damage in GaN-based materials and devices. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2013 , 31, 050801	2.9	145
164	Radiation effects in GaN materials and devices. <i>Journal of Materials Chemistry C</i> , 2013 , 1, 877-887	7.1	139
163	Temperature stability of high-resistivity GaN buffer layers grown by metalorganic chemical vapor deposition. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2013 , 31, 051208	1.3	13
162	Electrical properties of undoped GaN films grown by maskless epitaxial lateral overgrowth. <i>Journal of Applied Physics</i> , 2013 , 113, 083712	2.5	12
161	Effect of electron irradiation on AlGaIn/GaN and InAlN/GaN heterojunctions. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2013 , 31, 022206	1.3	19
160	Free-Standing GaN Layer by Combination of Electrochemical and Photo-Electrochemical Etching. <i>Applied Physics Express</i> , 2013 , 6, 061001	2.4	12
159	Deep centers and persistent photocapacitance in AlGaIn/GaN high electron mobility transistor structures grown on Si substrates. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2013 , 31, 011211	1.3	14
158	Radiation Damage in GaN-Based Materials and Devices 2013 , 1753-1764		1
157	Effect of buffer layer structure on electrical and structural properties of AlGaIn/GaN high electron mobility transistors. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2012 , 30, 011205	1.3	13
156	Comparison of neutron irradiation effects in AlGaIn/AlN/GaN, AlGaIn/GaN, and InAlN/GaN heterojunctions. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2012 , 30, 061207	1.3	28

155	Deep traps and enhanced photoluminescence efficiency in nonpolar a-GaN/InGaN quantum well structures. <i>Journal of Applied Physics</i> , 2012 , 111, 033103	2.5	4
154	Energy coupling processes in InGaN/GaN nanopillar light emitting diodes embedded with Ag and Ag/SiO ₂ nanoparticles. <i>Journal of Materials Chemistry</i> , 2012 , 22, 21749		18
153	Investigation of Optical and Structural Stability of Localized Surface Plasmon Mediated Light-Emitting Diodes by Ag and Ag/SiO ₂ Nanoparticles. <i>Advanced Functional Materials</i> , 2012 , 22, 2728-2734	15.6	53
152	Electrical properties and radiation detector performance of free-standing bulk n-GaN. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2012 , 30, 021205	1.3	26
151	Radiation Effects in GaN. <i>Springer Series in Materials Science</i> , 2012 , 251-294	0.9	6
150	Admittance Spectra Studies of Quantum Well States in AlGaN/AlN/GaN Heterojunctions. <i>ECS Journal of Solid State Science and Technology</i> , 2012 , 1, P152-P156	2	5
149	Metastable centers in AlGaN/AlN/GaN heterostructures. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2012 , 30, 041209	1.3	12
148	Enhanced light output of InGaN/GaN blue light emitting diodes with Ag nano-particles embedded in nano-needle layer. <i>Optics Express</i> , 2012 , 20, 6036-41	3.3	19
147	Localized surface plasmon enhanced quantum efficiency of InGaN/GaN quantum wells by Ag/SiO ₂ nanoparticles. <i>Optics Express</i> , 2012 , 20, 2116-23	3.3	32
146	Electrical and luminescent properties and deep traps spectra in GaN nanopillar layers prepared by dry etching. <i>Journal of Applied Physics</i> , 2012 , 112, 073112	2.5	14
145	Characteristics of a-GaN films and a-AlGaN/GaN heterojunctions prepared on r-sapphire by two-stage growth process. <i>Journal of Applied Physics</i> , 2011 , 110, 093709	2.5	8
144	The effect of neutron irradiation and annealing temperature on the electrical properties and lattice constant of epitaxial gallium nitride layers. <i>Semiconductors</i> , 2011 , 45, 134-140	0.7	5
143	Quantum efficiency control of InGaN/GaN multi-quantum-well structures using Ag/SiO ₂ core-shell nanoparticles. <i>Applied Physics Letters</i> , 2011 , 99, 251114	3.4	15
142	Deep traps and thermal measurements on AlGaN/GaN on Si transistors. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2011 , 29, 042201	1.3	5
141	Deep electron and hole traps in neutron transmutation doped n-GaN. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2011 , 29, 041201	1.3	16
140	Role of nonradiative recombination centers and extended defects in nonpolar GaN on light emission efficiency. <i>Applied Physics Letters</i> , 2011 , 98, 072104	3.4	30
139	Comparison of hole traps in n-GaN grown by hydride vapor phase epitaxy, metal organic chemical vapor deposition, and epitaxial lateral overgrowth. <i>Journal of Applied Physics</i> , 2011 , 109, 123701	2.5	41
138	10 MeV electrons irradiation effects in variously doped n-GaN. <i>Journal of Applied Physics</i> , 2011 , 109, 123703	2.03	22

137	Neutron doping effects in epitaxially laterally overgrown n-GaN. <i>Applied Physics Letters</i> , 2011 , 98, 212103.4	3.4	8
136	Carrier Removal Rates and Deep Traps in Neutron Irradiated n-GaN Films. <i>Journal of the Electrochemical Society</i> , 2011 , 158, H866	3.9	17
135	GaN as a detector of α particles and neutrons 2011 ,		9
134	Electrical and optical properties of Fe doped AlGa _N grown by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2010 , 107, 023708	2.5	4
133	a-plane GaN hydride vapor phase epitaxy on a-plane GaN templates with and without use of TiN intermediate layers. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2010 , 28, 1039-1043	1.3	1
132	GaN epitaxial films grown by hydride vapor phase epitaxy on polycrystalline chemical vapor deposition diamond substrates using surface nanostructuring with TiN or anodic Al oxide. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2010 , 28, 1011-1015	1.3	5
131	Neutron transmutation doping effects in GaN. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2010 , 28, 608-612	1.3	26
130	Shallow and Deep Centers in As-Grown and Annealed MgZnO/ZnO Structures with Quantum Wells. <i>Journal of Electronic Materials</i> , 2010 , 39, 601-607	1.9	4
129	Role of Hydrogen in the CVD of Wide Bandgap Nitride Semiconductors. <i>Chemical Vapor Deposition</i> , 2010 , 16, 266-274		8
128	Electrical properties and deep traps spectra of N-polar and Ga-polar AlGa _N films grown by molecular beam epitaxy in a wide composition range. <i>Journal of Applied Physics</i> , 2009 , 105, 113712	2.5	7
127	Electrical properties and deep traps spectra in undoped and Si-doped m-plane GaN films. <i>Journal of Applied Physics</i> , 2009 , 105, 063708	2.5	12
126	Comparison of electrical properties and deep traps in p-Al _x Ga _{1-x} N grown by molecular beam epitaxy and metal organic chemical vapor deposition. <i>Journal of Applied Physics</i> , 2009 , 106, 073706	2.5	13
125	Anisotropy of In incorporation in GaN/InGa _N multi-quantum wells prepared by epitaxial lateral overgrowth. <i>Applied Physics Letters</i> , 2009 , 94, 142103	3.4	16
124	Properties of undoped GaN/InGa _N multi-quantum-wells and GaN/InGa _N p-n junctions prepared by epitaxial lateral overgrowth. <i>Journal of Applied Physics</i> , 2009 , 105, 123708	2.5	10
123	Alpha particle detection with GaN Schottky diodes. <i>Journal of Applied Physics</i> , 2009 , 106, 103708	2.5	30
122	Persistent photoconductivity in MgZnO alloys. <i>Semiconductors</i> , 2009 , 43, 577-580	0.7	1
121	Nonpolar GaN grown on Si by hydride vapor phase epitaxy using anodized Al nanomask. <i>Applied Physics Letters</i> , 2009 , 94, 022114	3.4	10
120	Annealing effects on electrical properties of MgZnO films grown by pulsed laser deposition. <i>Journal of Applied Physics</i> , 2008 , 103, 083704	2.5	15

119	Electron irradiation of AlGaIn/GaN and AlN/GaN heterojunctions. <i>Applied Physics Letters</i> , 2008 , 93, 1521013,4		16
118	Electrical and structural properties of AlN/GaN and AlGaIn/GaN heterojunctions. <i>Journal of Applied Physics</i> , 2008 , 104, 053702	2.5	29
117	Improved crystalline quality nonpolar a-GaN films grown by hydride vapor phase epitaxy. <i>Journal of Vacuum Science & Technology B</i> , 2008 , 26, 1937-1941		4
116	Effects of laterally overgrown n-GaN thickness on defect and deep level concentrations. <i>Journal of Vacuum Science & Technology B</i> , 2008 , 26, 990		36
115	Electron Irradiation Effects in GaN/InGaN Multiple Quantum Well Structures. <i>Journal of the Electrochemical Society</i> , 2008 , 155, H31	3.9	12
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